

## NCE P-Channel Super Trench Power MOSFET

### Description

The NCEP01P60G uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(on)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

### General Features

- $V_{DS} = -100V, I_D = -55A$   
 $R_{DS(on)} = 22m\Omega$  (typical) @  $V_{GS} = -10V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating

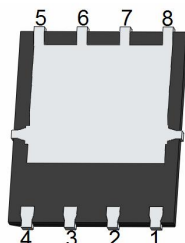
**100% UIS TESTED!**

**100%  $\Delta V_{ds}$  TESTED!**

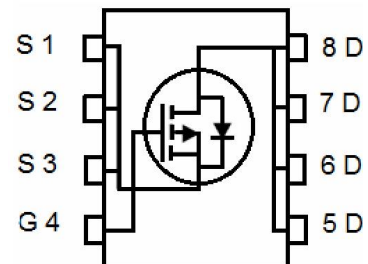
### DFN 5X6



Top View



Bottom View



Schematic Diagram

### Package Marking and Ordering Information

| Device Marking | Device     | Device Package | Reel Size | Tape width | Quantity |
|----------------|------------|----------------|-----------|------------|----------|
| P01P60G        | NCEP01P60G | DFN5X6-8L      | -         | -          | -        |

### Absolute Maximum Ratings ( $T_c = 25^\circ\text{C}$ unless otherwise noted)

| Parameter   | Symbol                   | Limit      | Unit                |
|---|--------------------------|------------|---------------------|
| Drain-Source Voltage                                  | $V_{DS}$                 | -100       | V                   |
| Gate-Source Voltage                                   | $V_{GS}$                 | $\pm 20$   | V                   |
| Drain Current-Continuous                              | $I_D$                    | -55        | A                   |
| Drain Current-Continuous( $T_c = 100^\circ\text{C}$ ) | $I_D(100^\circ\text{C})$ | -39        | A                   |
| Pulsed Drain Current                                  | $I_{DM}$                 | -220       | A                   |
| Maximum Power Dissipation                             | $P_D$                    | 140        | W                   |
| Derating factor                                       |                          | 1.12       | W/ $^\circ\text{C}$ |
| Single pulse avalanche energy (Note 1)                | $E_{AS}$                 | 670        | mJ                  |
| Operating Junction and Storage Temperature Range      | $T_J, T_{STG}$           | -55 To 150 | $^\circ\text{C}$    |

### Thermal Characteristic

|                                      |                 |      |                    |
|--------------------------------------|-----------------|------|--------------------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 0.89 | $^\circ\text{C/W}$ |
|--------------------------------------|-----------------|------|--------------------|

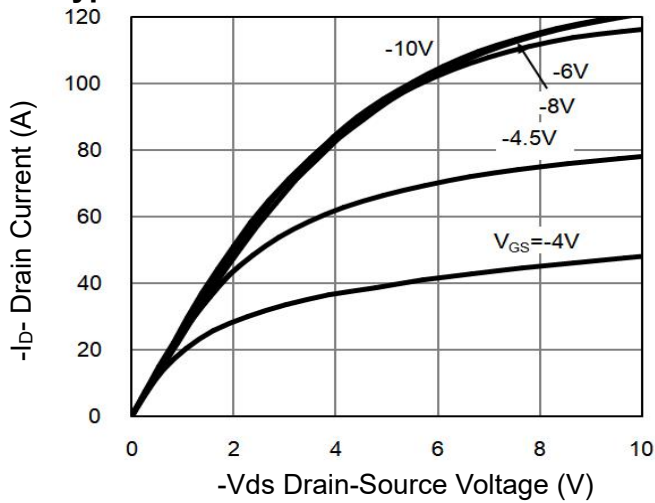
## Electrical Characteristics (T<sub>c</sub>=25°C unless otherwise noted)

| Parameter   | Symbol              | Condition  | Min  | Typ  | Max  | Unit |
|---|---------------------|--|------|------|------|------|
| Off Characteristics                               |                     |  |      |      |      |      |
| Drain-Source Breakdown Voltage                    | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V I <sub>D</sub> =-250μA   | -100 |      | -    | V    |
| Zero Gate Voltage Drain Current                   | I <sub>DSS</sub>    | V <sub>DS</sub> =-100V, V <sub>GS</sub> =0V  | -    | -    | -1   | μA   |
| Gate-Body Leakage Current                         | I <sub>GSS</sub>    | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V   | -    | -    | ±100 | nA   |
| On Characteristics                                |                     |  |      |      |      |      |
| Gate Threshold Voltage                            | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA                                  | -2.0 | -3.0 | -4.0 | V    |
| Drain-Source On-State Resistance                  | R <sub>DS(ON)</sub> | V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A  | -    | 22   | 29   | mΩ   |
| Forward Transconductance                          | g <sub>FS</sub>     | V <sub>DS</sub> =-5V, I <sub>D</sub> =-20A   | -    | 30   | -    | S    |
| Dynamic Characteristics                           |                     |  |      |      |      |      |
| Input Capacitance                                 | C <sub>iss</sub>    | V <sub>DS</sub> =-50V, V <sub>GS</sub> =0V,<br>F=1.0MHz                                    | -    | 4900 | -    | PF   |
| Output Capacitance                                | C <sub>oss</sub>    |  | -    | 435  | -    | PF   |
| Reverse Transfer Capacitance                      | C <sub>rss</sub>    |  | -    | 9.5  | -    | PF   |
| Switching Characteristics <small>(Note 2)</small> |                     |  |      |      |      |      |
| Turn-on Delay Time                                | t <sub>d(on)</sub>  | V <sub>DD</sub> =-50V, I <sub>D</sub> =-20A<br>V <sub>GS</sub> =-10V, R <sub>G</sub> =1.6Ω | -    | 15   | -    | nS   |
| Turn-on Rise Time                                 | t <sub>r</sub>      |  | -    | 18   | -    | nS   |
| Turn-Off Delay Time                               | t <sub>d(off)</sub> |  | -    | 50   | -    | nS   |
| Turn-Off Fall Time                                | t <sub>f</sub>      |  | -    | 18   | -    | nS   |
| Total Gate Charge                                 | Q <sub>g</sub>      | V <sub>DS</sub> =-50V, I <sub>D</sub> =-20A,<br>V <sub>GS</sub> =-10V                      | -    | 61   | -    | nC   |
| Gate-Source Charge                                | Q <sub>gs</sub>     |  | -    | 17   | -    | nC   |
| Gate-Drain Charge                                 | Q <sub>gd</sub>     |  | -    | 8.5  | -    | nC   |
| Drain-Source Diode Characteristics                |                     |  |      |      |      |      |
| Diode Forward Voltage                             | V <sub>SD</sub>     | V <sub>GS</sub> =0V, I <sub>S</sub> =-20A  | -    |      | -1.2 | V    |
| Diode Forward Current                             | I <sub>S</sub>      |  | -    | -    | -55  | A    |
| Reverse Recovery Time                             | t <sub>rr</sub>     | T <sub>J</sub> = 25°C, I <sub>F</sub> =-20A  | -    | 55   | -    | nS   |
| Reverse Recovery Charge                           | Q <sub>rr</sub>     | di/dt = 100A/μs  | -    | 101  | -    | nC   |

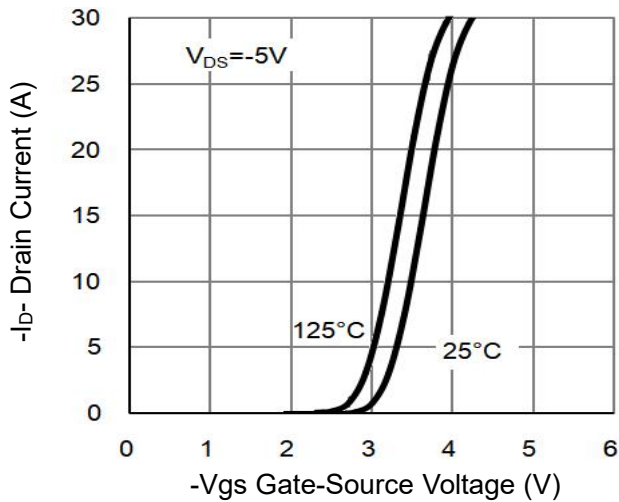
### Notes:

1. EAS condition : T<sub>j</sub>=25°C, V<sub>DD</sub>=-50V, V<sub>G</sub>=-10V, L=0.5mH, R<sub>g</sub>=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J</sub>(MAX)=150°C. The SOA curve provides a single pulse rating.

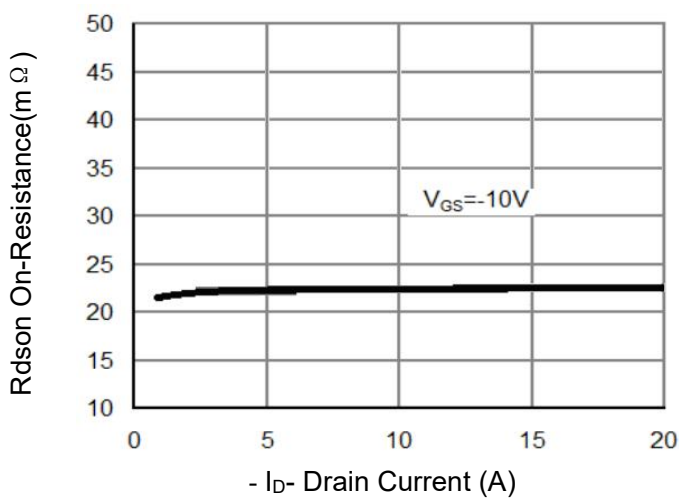
## Typical Electrical and Thermal Characteristics



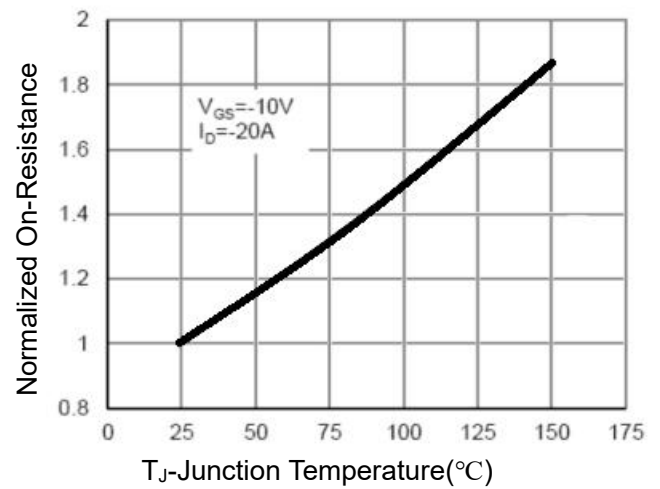
**Figure 1 Output Characteristics**



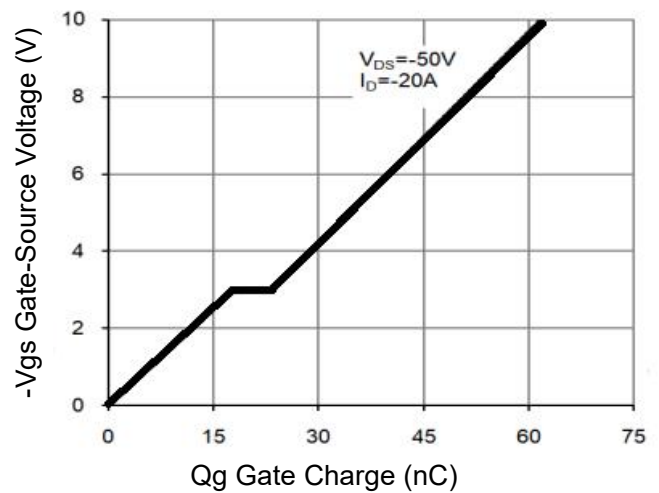
**Figure 2 Transfer Characteristics**



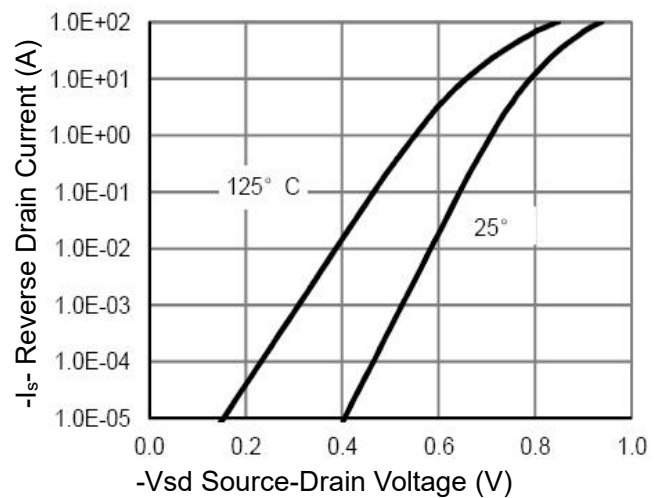
**Figure 3 Rdson- Drain Current**



**Figure 4 Rdson-Junction Temperature**



**Figure 5 Gate Charge**



**Figure 6 Source- Drain Diode Forward**

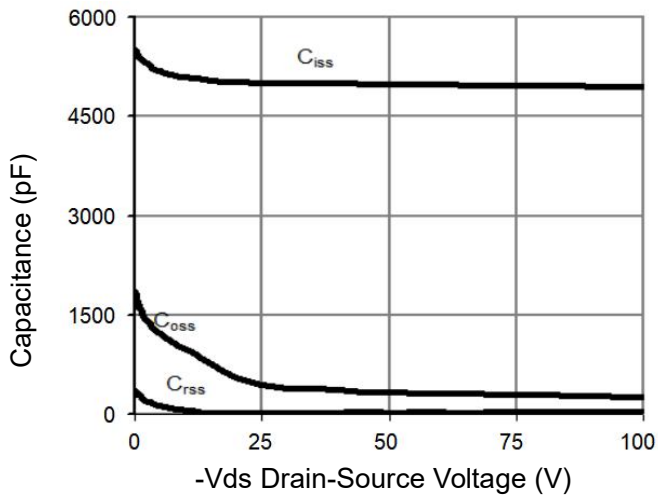


Figure 7 Capacitance vs Vds

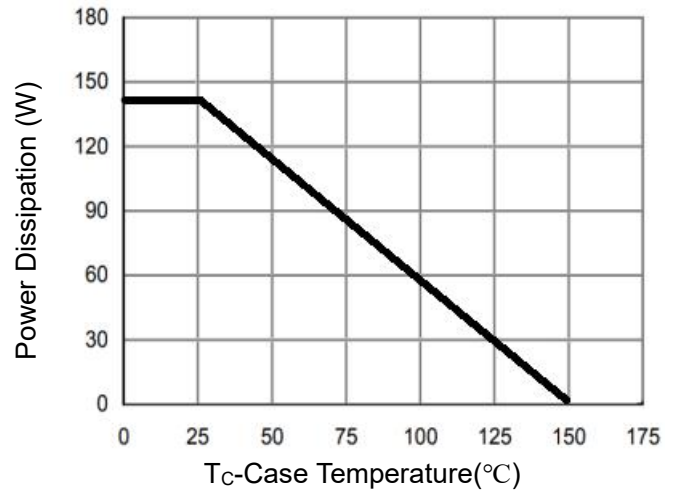


Figure 9 Power De-rating

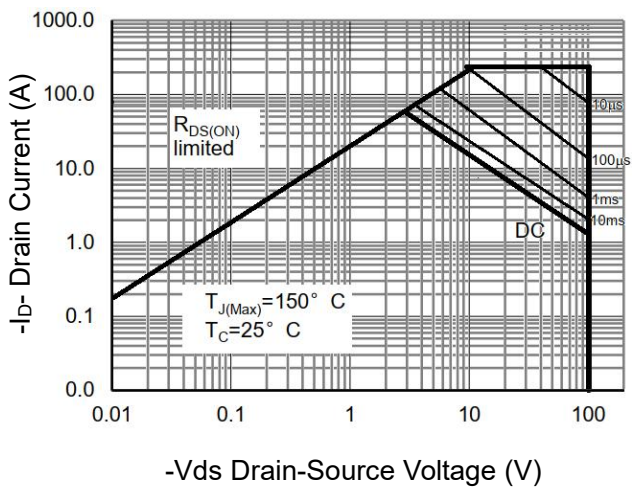


Figure 8 Safe Operation Area (Note 3)

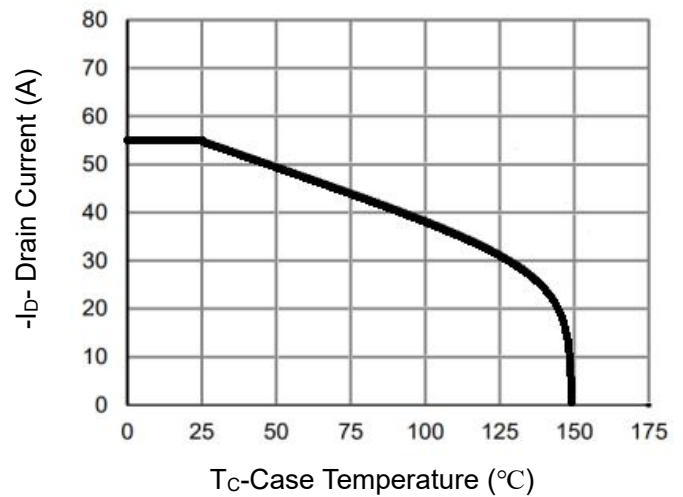


Figure 10 Current De-rating

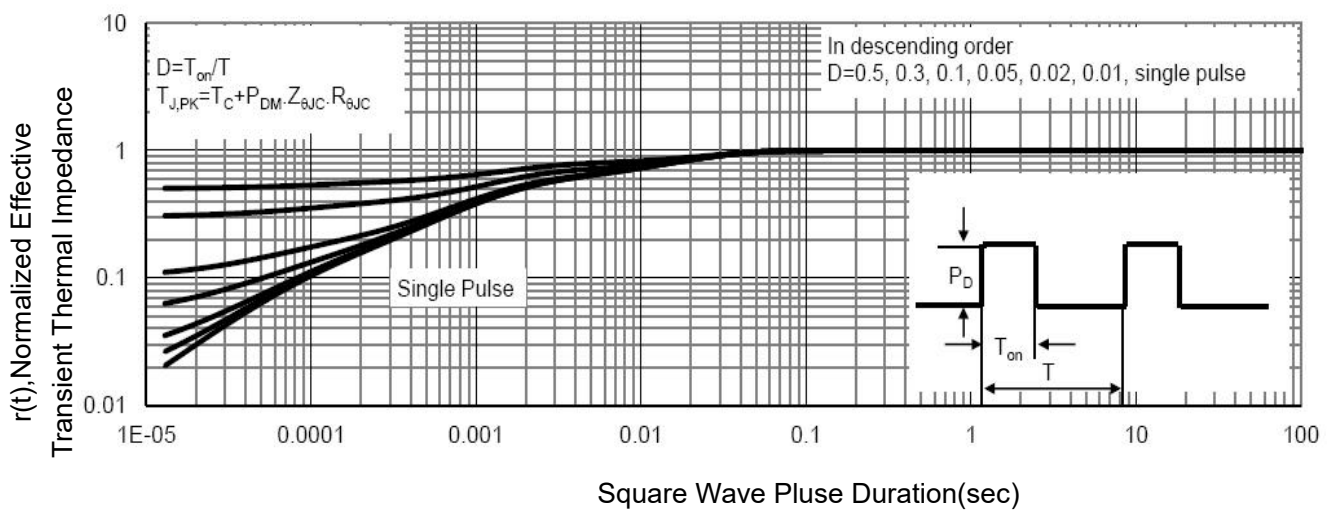
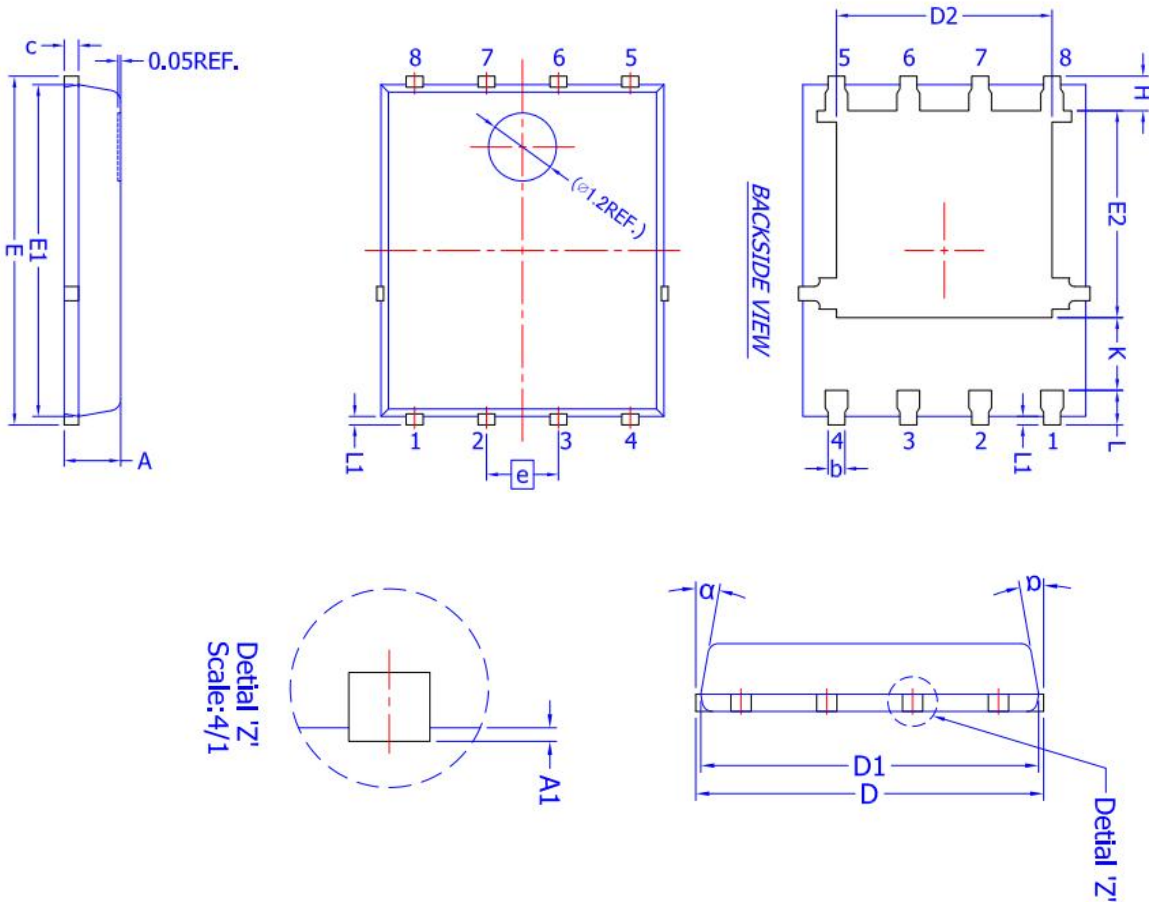


Figure 11 Normalized Maximum Transient Thermal Impedance

## DFN5X6-8L Package Information



| DIM. | MILLIMETERS |      |      |
|------|-------------|------|------|
|      | MIN.        | NOM. | MAX. |
| A    | 0.90        | 1.00 | 1.10 |
| A1   | 0           | -    | 0.05 |
| b    | 0.30        | 0.40 | 0.50 |
| c    | 0.20        | 0.25 | 0.30 |
| D    | 5.15 BSC    |      |      |
| D1   | 5.00 BSC    |      |      |
| D2   | 3.76        | 3.81 | 3.86 |
| E    | 6.15 BSC    |      |      |
| E1   | 5.80        | 5.85 | 5.90 |
| E2   | 3.45        | 3.65 | 3.85 |
| e    | 1.27 BSC    |      |      |
| H    | 0.51        | 0.61 | 0.71 |
| K    | 1.10        | -    | -    |
| L    | 0.51        | 0.61 | 0.71 |
| L1   | 0.08        | 0.15 | 0.23 |
| α    | 10°         | 11°  | 12°  |

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